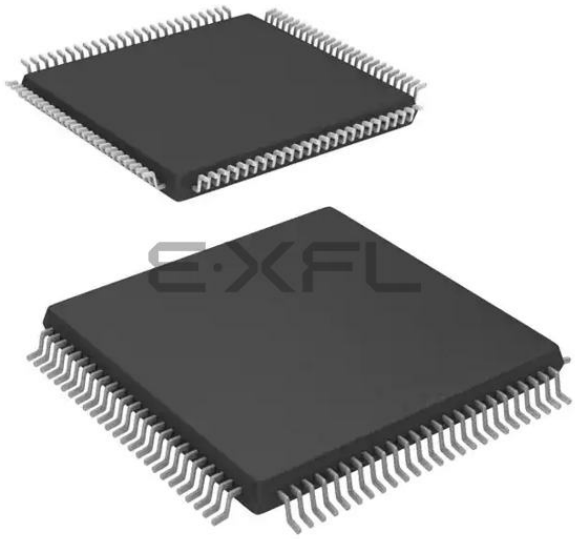


Welcome to E-XFL.COM

Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	72
Number of Logic Elements/Cells	576
Total RAM Bits	6144
Number of I/O	66
Number of Gates	31000
Voltage - Supply	3V ~ 3.6V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	100-TQFP
Supplier Device Package	100-TQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/intel/epf10k10atc100-1

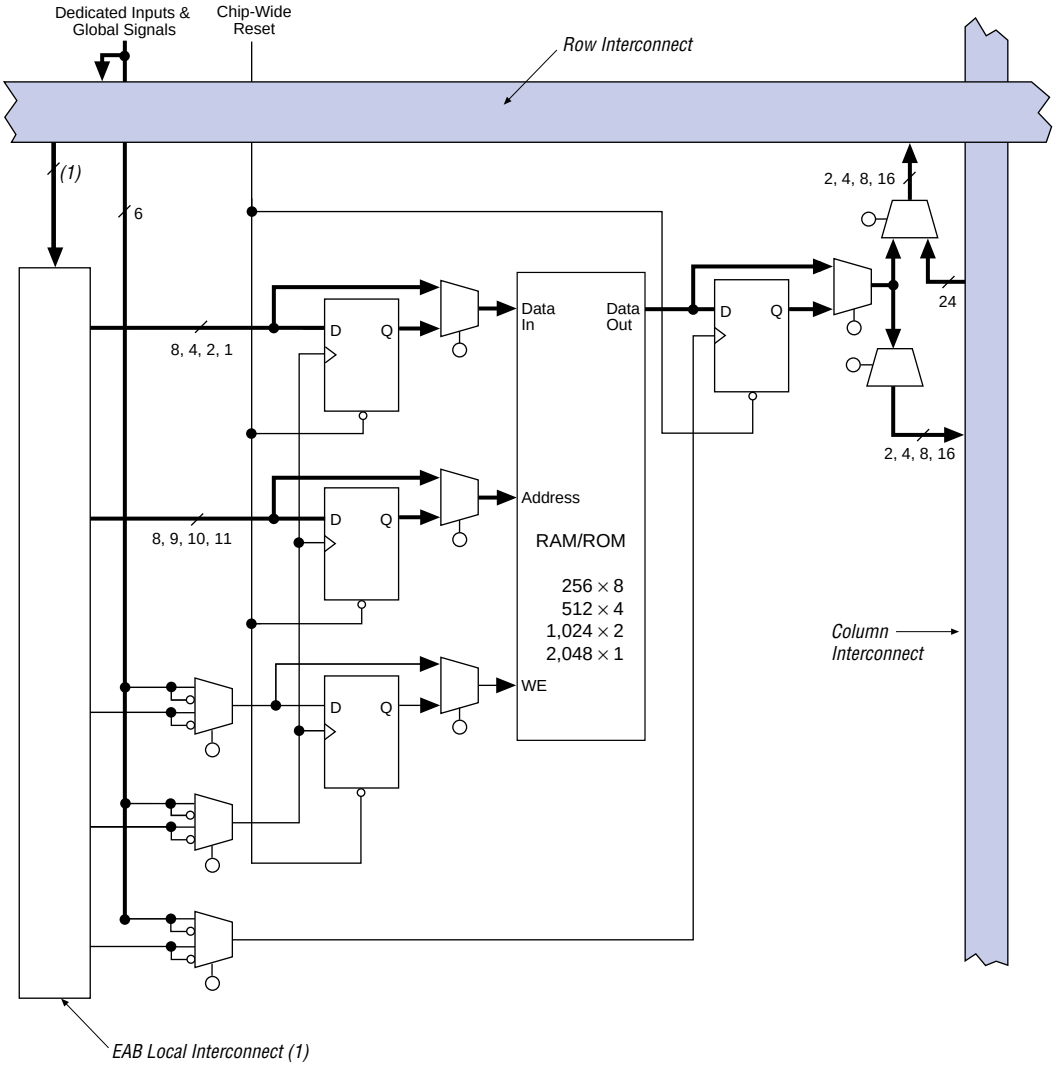
The FLEX 10K architecture is similar to that of embedded gate arrays, the fastest-growing segment of the gate array market. As with standard gate arrays, embedded gate arrays implement general logic in a conventional "sea-of-gates" architecture. In addition, embedded gate arrays have dedicated die areas for implementing large, specialized functions. By embedding functions in silicon, embedded gate arrays provide reduced die area and increased speed compared to standard gate arrays. However, embedded megafunctions typically cannot be customized, limiting the designer's options. In contrast, FLEX 10K devices are programmable, providing the designer with full control over embedded megafunctions and general logic while facilitating iterative design changes during debugging.

Each FLEX 10K device contains an embedded array and a logic array. The embedded array is used to implement a variety of memory functions or complex logic functions, such as digital signal processing (DSP), microcontroller, wide-data-path manipulation, and data-transformation functions. The logic array performs the same function as the sea-of-gates in the gate array: it is used to implement general logic, such as counters, adders, state machines, and multiplexers. The combination of embedded and logic arrays provides the high performance and high density of embedded gate arrays, enabling designers to implement an entire system on a single device.

FLEX 10K devices are configured at system power-up with data stored in an Altera serial configuration device or provided by a system controller. Altera offers the EPC1, EPC2, EPC16, and EPC1441 configuration devices, which configure FLEX 10K devices via a serial data stream. Configuration data can also be downloaded from system RAM or from Altera's BitBlaster™ serial download cable or ByteBlasterMV™ parallel port download cable. After a FLEX 10K device has been configured, it can be reconfigured in-circuit by resetting the device and loading new data. Because reconfiguration requires less than 320 ms, real-time changes can be made during system operation.

FLEX 10K devices contain an optimized interface that permits microprocessors to configure FLEX 10K devices serially or in parallel, and synchronously or asynchronously. The interface also enables microprocessors to treat a FLEX 10K device as memory and configure the device by writing to a virtual memory location, making it very easy for the designer to reconfigure the device.

Figure 4. FLEX 10K Embedded Array Block



Note:

(1) EPF10K10, EPF10K10A, EPF10K20, EPF10K30, EPF10K30A, EPF10K40, EPF10K50, and EPF10K50V devices have 22 EAB local interconnect channels; EPF10K70, EPF10K100, EPF10K100A, EPF10K130V, and EPF10K250A devices have 26.

Table 12 describes the FLEX 10K device supply voltages and MultiVolt I/O support levels.

Table 12. Supply Voltages & MultiVolt I/O Support Levels

Devices	Supply Voltage (V)		MultiVolt I/O Support Levels (V)	
	V_{CCINT}	V_{CCIO}	Input	Output
FLEX 10K *(1)*	5.0	5.0	3.3 or 5.0	5.0
	5.0	3.3	3.3 or 5.0	3.3 or 5.0
EPF10K50V *(1)*	3.3	3.3	3.3 or 5.0	3.3 or 5.0
EPF10K130V	3.3	3.3	3.3 or 5.0	3.3 or 5.0
FLEX 10KA *(1)*	3.3	3.3	2.5, 3.3, or 5.0	3.3 or 5.0
	3.3	2.5	2.5, 3.3, or 5.0	2.5

Note
(1) 240-pin QFP packages do not support the MultiVolt I/O features, so they do not have separate V_{CCIO} pins.

Power Sequencing & Hot-Socketing

Because FLEX 10K devices can be used in a multi-voltage environment, they have been designed specifically to tolerate any possible power-up sequence. The V_{CCIO} and V_{CCINT} power supplies can be powered in any order.

Signals can be driven into FLEX 10KA devices before and during power up without damaging the device. Additionally, FLEX 10KA devices do not drive out during power up. Once operating conditions are reached, FLEX 10KA devices operate as specified by the user.

IEEE Std. 1149.1 (JTAG) Boundary-Scan Support

All FLEX 10K devices provide JTAG BST circuitry that complies with the IEEE Std. 1149.1-1990 specification. All FLEX 10K devices can also be configured using the JTAG pins through the BitBlaster serial download cable, or ByteBlasterMV parallel port download cable, or via hardware that uses the Jam™ programming and test language. JTAG BST can be performed before or after configuration, but not during configuration. FLEX 10K devices support the JTAG instructions shown in Table 13.

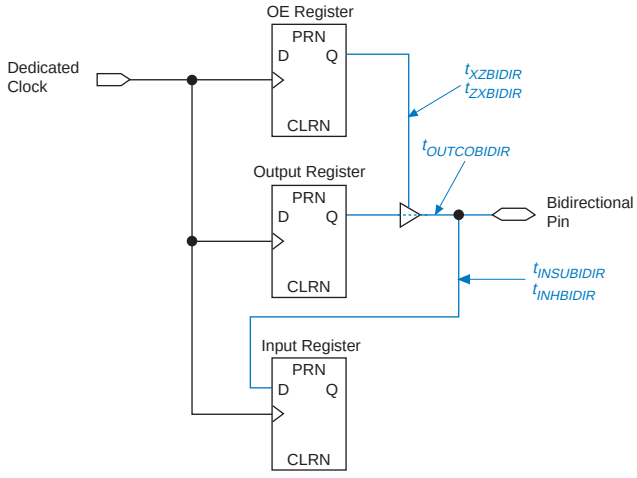
Table 18. FLEX 10K 5.0-V Device Recommended Operating Conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CCINT}	Supply voltage for internal logic and input buffers	*(3)*, *(4)*	4.75 (4.50)	5.25 (5.50)	V
V_{CCIO}	Supply voltage for output buffers, 5.0-V operation	*(3)*, *(4)*	4.75 (4.50)	5.25 (5.50)	V
	Supply voltage for output buffers, 3.3-V operation	*(3)*, *(4)*	3.00 (3.00)	3.60 (3.60)	V
V_I	Input voltage		–0.5	V_{CCINT} + 0.5	V
V_O	Output voltage		0	V_{CCIO}	V
T_A	Ambient temperature	For commercial use	0	70	° C
		For industrial use	–40	85	° C
T_J	Operating temperature	For commercial use	0	85	° C
		For industrial use	–40	100	° C
t_R	Input rise time			40	ns
t_F	Input fall time			40	ns

Table 27. FLEX 10KA 3.3-V Device Recommended Operating Conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CCINT}	Supply voltage for internal logic and input buffers	*(3)*, *(4)*	3.00 (3.00)	3.60 (3.60)	V
V_{CCIO}	Supply voltage for output buffers, 3.3-V operation	*(3)*, *(4)*	3.00 (3.00)	3.60 (3.60)	V
	Supply voltage for output buffers, 2.5-V operation	*(3)*, *(4)*	2.30 (2.30)	2.70 (2.70)	V
V_I	Input voltage	*(5)*	–0.5	5.75	V
V_O	Output voltage		0	V_{CCIO}	V
T_A	Ambient temperature	For commercial use	0	70	° C
		For industrial use	–40	85	° C
T_J	Operating temperature	For commercial use	0	85	° C
		For industrial use	–40	100	° C
t_R	Input rise time			40	ns
t_F	Input fall time			40	ns

Figure 28. Synchronous Bidirectional Pin External Timing Model



Tables 32 through 36 describe the FLEX 10K device internal timing parameters. These internal timing parameters are expressed as worst-case values. Using hand calculations, these parameters can be used to estimate design performance. However, before committing designs to silicon, actual worst-case performance should be modeled using timing simulation and analysis. Tables 37 through 38 describe FLEX 10K external timing parameters.

Table 32. LE Timing Microparameters (Part 1 of 2) *Note (1)*

Symbol	Parameter	Conditions
t_{LUT}	LUT delay for data-in	
t_{CLUT}	LUT delay for carry-in	
t_{RLUT}	LUT delay for LE register feedback	
t_{PACKED}	Data-in to packed register delay	
t_{EN}	LE register enable delay	
t_{CICO}	Carry-in to carry-out delay	
t_{CGEN}	Data-in to carry-out delay	
t_{CGENR}	LE register feedback to carry-out delay	
t_{CASC}	Cascade-in to cascade-out delay	
t_{C}	LE register control signal delay	
t_{CO}	LE register clock-to-output delay	
t_{COMB}	Combinatorial delay	

Tables 39 through 47 show EPF10K10 and EPF10K20 device internal and external timing parameters.

Table 39. EPF10K10 & EPF10K20 Device LE Timing Microparameters *Note (1)*

Symbol	-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	
t_{LUT}		1.4		1.7	ns
t_{CLUT}		0.6		0.7	ns
t_{RLUT}		1.5		1.9	ns
t_{PACKED}		0.6		0.9	ns
t_{EN}		1.0		1.2	ns
t_{CICO}		0.2		0.3	ns
t_{CGEN}		0.9		1.2	ns
t_{CGENR}		0.9		1.2	ns
t_{CASC}		0.8		0.9	ns
t_{C}		1.3		1.5	ns
t_{CO}		0.9		1.1	ns
t_{COMB}		0.5		0.6	ns
t_{SU}	1.3		2.5		ns
t_{H}	1.4		1.6		ns
t_{PRE}		1.0		1.2	ns
t_{CLR}		1.0		1.2	ns
t_{CH}	4.0		4.0		ns
t_{CL}	4.0		4.0		ns

Table 40. EPF10K10 & EPF10K20 Device IOE Timing Microparameters *Note (1)*

Symbol	-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	
t_{IOD}		1.3		1.6	ns
t_{IOC}		0.5		0.7	ns
t_{IOCO}		0.2		0.2	ns
t_{IOCOMB}		0.0		0.0	ns
t_{IOSU}	2.8		3.2		ns
t_{IOH}	1.0		1.2		ns
t_{IOCLR}		1.0		1.2	ns
t_{OD1}		2.6		3.5	ns
t_{OD2}		4.9		6.4	ns
t_{OD3}		6.3		8.2	ns
t_{XZ}		4.5		5.4	ns
t_{ZX1}		4.5		5.4	ns
t_{ZX2}		6.8		8.3	ns
t_{ZX3}		8.2		10.1	ns
t_{INREG}		6.0		7.5	ns
t_{IOFD}		3.1		3.5	ns
t_{INCOMB}		3.1		3.5	ns

Table 54. EPF10K50 Device Interconnect Timing Microparameters *Note (1)*

Symbol	-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	
$t_{DIN2IOE}$		8.4		10.2	ns
t_{DIN2LE}		3.6		4.8	ns
$t_{DIN2DATA}$		5.5		7.2	ns
$t_{DCLK2IOE}$		4.6		6.2	ns
$t_{DCLK2LE}$		3.6		4.8	ns
$t_{SAMELAB}$		0.3		0.3	ns
$t_{SAMEROW}$		3.3		3.7	ns
$t_{SAMECOLUMN}$		3.9		4.1	ns
$t_{DIFFROW}$		7.2		7.8	ns
$t_{TWOROWS}$		10.5		11.5	ns
$t_{LEPERIPH}$		7.5		8.2	ns
$t_{LABCARRY}$		0.4		0.6	ns
$t_{LABCASC}$		2.4		3.0	ns

Table 55. EPF10K30, EPF10K40 & EPF10K50 Device External Timing Parameters *Note (1)*

Symbol	-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	
t_{DRR}		17.2		21.1	ns
t_{INSU} *(2)*, *(3)*	5.7		6.4		ns
t_{INH} *(3)*	0.0		0.0		ns
t_{OUTCO} *(3)*	2.0	8.8	2.0	11.2	ns

Table 56. EPF10K30, EPF10K40 & EPF10K50 Device External Bidirectional Timing Parameters *Note (1)*

Symbol	-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	
$t_{INSUBIDIR}$	4.1		4.6		ns
$t_{INHBIDIR}$	0.0		0.0		ns
$t_{OUTCOBIDIR}$	2.0	8.8	2.0	11.2	ns
$t_{XZBIDIR}$		12.3		15.0	ns
$t_{ZXBIDIR}$		12.3		15.0	ns

Table 60. EPF10K70 Device EAB Internal Timing Macroparameters *Note (1)*							
Symbol	**-2 Speed Grade**		**-3 Speed Grade**		**-4 Speed Grade**		**Unit**
	Min	**Max**	**Min**	**Max**	**Min**	**Max**	
t_{EABAA}		12.1		13.7		17.0	ns
$t_{EABRCCOMB}$	12.1		13.7		17.0		ns
$t_{EABRCREG}$	8.6		9.7		11.9		ns
t_{EABWP}	5.2		5.8		7.2		ns
$t_{EABWCCOMB}$	6.5		7.3		9.0		ns
$t_{EABWCREG}$	11.6		13.0		16.0		ns
t_{EABDD}		8.8		10.0		12.5	ns
$t_{EABDATACO}$		1.7		2.0		3.4	ns
$t_{EABDATASU}$	4.7		5.3		5.6		ns
$t_{EABDATAH}$	0.0		0.0		0.0		ns
$t_{EABWESU}$	4.9		5.5		5.8		ns
t_{EABWEH}	0.0		0.0		0.0		ns
$t_{EABWDSU}$	1.8		2.1		2.7		ns
t_{EABWDH}	0.0		0.0		0.0		ns
$t_{EABWASU}$	4.1		4.7		5.8		ns
t_{EABWAH}	0.0		0.0		0.0		ns
t_{EABWO}		8.4		9.5		11.8	ns

Table 68. EPF10K100 Device Interconnect Timing Microparameters *Note (1)*

Symbol	-3DX Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{DIN2IOE}$		10.3		10.3		12.2	ns
t_{DIN2LE}		4.8		4.8		6.0	ns
$t_{DIN2DATA}$		7.3		7.3		11.0	ns
$t_{DCLK2IOE}$ without ClockLock or ClockBoost circuitry		6.2		6.2		7.7	ns
$t_{DCLK2IOE}$ with ClockLock or ClockBoost circuitry		2.3		–		–	ns
$t_{DCLK2LE}$ without ClockLock or ClockBoost circuitry		4.8		4.8		6.0	ns
$t_{DCLK2LE}$ with ClockLock or ClockBoost circuitry		2.3		–		–	ns
$t_{SAMELAB}$		0.4		0.4		0.5	ns
$t_{SAMEROW}$		4.9		4.9		5.5	ns
$t_{SAMECOLUMN}$		5.1		5.1		5.4	ns
$t_{DIFFROW}$		10.0		10.0		10.9	ns
$t_{TWOROWS}$		14.9		14.9		16.4	ns
$t_{LEPERIPH}$		6.9		6.9		8.1	ns
$t_{LABCARRY}$		0.9		0.9		1.1	ns
$t_{LABCASC}$		3.0		3.0		3.2	ns

Table 72. EPF10K50V Device IOE Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{IOD}		1.2		1.6		1.9		2.1	ns
t_{IOC}		0.3		0.4		0.5		0.5	ns
t_{IOCO}		0.3		0.3		0.4		0.4	ns
t_{IOCOMB}		0.0		0.0		0.0		0.0	ns
t_{IOSU}	2.8		2.8		3.4		3.9		ns
t_{IOH}	0.7		0.8		1.0		1.4		ns
t_{IOCLR}		0.5		0.6		0.7		0.7	ns
t_{OD1}		2.8		3.2		3.9		4.7	ns
t_{OD2}		–		–		–		–	ns
t_{OD3}		6.5		6.9		7.6		8.4	ns
t_{XZ}		2.8		3.1		3.8		4.6	ns
t_{ZX1}		2.8		3.1		3.8		4.6	ns
t_{ZX2}		–		–		–		–	ns
t_{ZX3}		6.5		6.8		7.5		8.3	ns
t_{INREG}		5.0		5.7		7.0		9.0	ns
t_{IOFD}		1.5		1.9		2.3		2.7	ns
t_{INCOMB}		1.5		1.9		2.3		2.7	ns

Notes to tables:
(1) All timing parameters are described in Tables 32 through 38 in this data sheet.
(2) Using an LE to register the signal may provide a lower setup time.
(3) This parameter is specified by characterization.

Tables 78 through 84 show EPF10K130V device internal and external timing parameters.

Table 78. EPF10K130V Device LE Timing Microparameters *Note (1)*

Symbol	-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{LUT}		1.3		1.8		2.3	ns
t_{CLUT}		0.5		0.7		0.9	ns
t_{RLUT}		1.2		1.7		2.2	ns
t_{PACKED}		0.5		0.6		0.7	ns
t_{EN}		0.6		0.8		1.0	ns
t_{CICO}		0.2		0.3		0.4	ns
t_{CGEN}		0.3		0.4		0.5	ns
t_{CGENR}		0.7		1.0		1.3	ns
t_{CASC}		0.9		1.2		1.5	ns
t_{C}		1.9		2.4		3.0	ns
t_{CO}		0.6		0.9		1.1	ns
t_{COMB}		0.5		0.7		0.9	ns
t_{SU}	0.2		0.2		0.3		ns
t_{H}	0.0		0.0		0.0		ns
t_{PRE}		2.4		3.1		3.9	ns
t_{CLR}		2.4		3.1		3.9	ns
t_{CH}	4.0		4.0		4.0		ns
t_{CL}	4.0		4.0		4.0		ns

Table 81. EPF10K130V Device EAB Internal Timing Macroparameters *Note (1)*							
Symbol	**-2 Speed Grade**		**-3 Speed Grade**		**-4 Speed Grade**		**Unit**
	Min	**Max**	**Min**	**Max**	**Min**	**Max**	
t_{EABAA}		11.2		14.2		14.2	ns
$t_{EABRCCOMB}$	11.1		14.2		14.2		ns
$t_{EABRCREG}$	8.5		10.8		10.8		ns
t_{EABWP}	3.7		4.7		4.7		ns
$t_{EABWCCOMB}$	7.6		9.7		9.7		ns
$t_{EABWCREG}$	14.0		17.8		17.8		ns
t_{EABDD}		11.1		14.2		14.2	ns
$t_{EABDATACO}$		3.6		4.6		4.6	ns
$t_{EABDATASU}$	4.4		5.6		5.6		ns
$t_{EABDATAH}$	0.0		0.0		0.0		ns
$t_{EABWESU}$	4.4		5.6		5.6		ns
t_{EABWEH}	0.0		0.0		0.0		ns
$t_{EABWDSU}$	4.6		5.9		5.9		ns
t_{EABWDH}	0.0		0.0		0.0		ns
$t_{EABWASU}$	3.9		5.0		5.0		ns
t_{EABWAH}	0.0		0.0		0.0		ns
t_{EABWO}		11.1		14.2		14.2	ns

Table 82. EPF10K130V Device Interconnect Timing Microparameters *Note (1)*

Symbol	-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{DIN2IOE}$		8.0		9.0		9.5	ns
t_{DIN2LE}		2.4		3.0		3.1	ns
$t_{DIN2DATA}$		5.0		6.3		7.4	ns
$t_{DCLK2IOE}$		3.6		4.6		5.1	ns
$t_{DCLK2LE}$		2.4		3.0		3.1	ns
$t_{SAMELAB}$		0.4		0.6		0.8	ns
$t_{SAMEROW}$		4.5		5.3		6.5	ns
$t_{SAMECOLUMN}$		9.0		9.5		9.7	ns
$t_{DIFFROW}$		13.5		14.8		16.2	ns
$t_{TWOROWS}$		18.0		20.1		22.7	ns
$t_{LEPERIPH}$		8.1		8.6		9.5	ns
$t_{LABCARRY}$		0.6		0.8		1.0	ns
$t_{LABCASC}$		0.8		1.0		1.2	ns

Table 83. EPF10K130V Device External Timing Parameters *Note (1)*

Symbol	-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{DRR}		15.0		19.1		24.2	ns
t_{INSU} *(2)*, *(3)*	6.9		8.6		11.0		ns
t_{INH} *(3)*	0.0		0.0		0.0		ns
t_{OUTCO} *(3)*	2.0	7.8	2.0	9.9	2.0	11.3	ns

Table 84. EPF10K130V Device External Bidirectional Timing Parameters *Note (1)*

Symbol	-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$	6.7		8.5		10.8		ns
$t_{INHBIDIR}$	0.0		0.0		0.0		ns
$t_{OUTCOBIDIR}$	2.0	6.9	2.0	8.8	2.0	10.2	ns
$t_{XZBIDIR}$		12.9		16.4		19.3	ns
$t_{ZXBIDIR}$		12.9		16.4		19.3	ns

Notes to tables:
(1) All timing parameters are described in Tables 32 through 38 in this data sheet.
(2) Using an LE to register the signal may provide a lower setup time.
(3) This parameter is specified by characterization.

Tables 85 through 91 show EPF10K10A device internal and external timing parameters.

Table 85. EPF10K10A Device LE Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{LUT}		0.9		1.2		1.6	ns
t_{CLUT}		1.2		1.4		1.9	ns
t_{RLUT}		1.9		2.3		3.0	ns
t_{PACKED}		0.6		0.7		0.9	ns
t_{EN}		0.5		0.6		0.8	ns
t_{CICO}		02		0.3		0.4	ns
t_{CGEN}		0.7		0.9		1.1	ns
t_{CGENR}		0.7		0.9		1.1	ns
t_{CASC}		1.0		1.2		1.7	ns
t_{C}		1.2		1.4		1.9	ns
t_{CO}		0.5		0.6		0.8	ns
t_{COMB}		0.5		0.6		0.8	ns
t_{SU}	1.1		1.3		1.7		ns
t_{H}	0.6		0.7		0.9		ns
t_{PRE}		0.5		0.6		0.9	ns
t_{CLR}		0.5		0.6		0.9	ns
t_{CH}	3.0		3.5		4.0		ns
t_{CL}	3.0		3.5		4.0		ns

Table 86. EPF10K10A Device IOE Timing Microparameters *Note (1)* **(Part 1 of 2)**

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
		1.3		1.5		2.0	ns
t_{IOC}		0.2		0.3		0.3	ns
t_{IOCO}		0.2		0.3		0.4	ns
t_{IOCOMB}		0.6		0.7		0.9	ns
t_{IOSU}	0.8		1.0		1.3		ns

Table 88. EPF10K10A Device EAB Internal Timing Macroparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{EABAA}		8.1		9.8		13.1	ns
$t_{EABRCCOMB}$	8.1		9.8		13.1		ns
$t_{EABRCREG}$	5.8		6.9		9.3		ns
t_{EABWP}	2.0		2.4		3.2		ns
$t_{EABWCCOMB}$	3.5		4.2		5.6		ns
$t_{EABWCREG}$	9.4		11.2		14.8		ns
t_{EABDD}		6.9		8.3		11.0	ns
$t_{EABDATACO}$		1.3		1.5		2.0	ns
$t_{EABDATASU}$	2.4		3.0		3.9		ns
$t_{EABDATAH}$	0.0		0.0		0.0		ns
$t_{EABWESU}$	4.1		4.9		6.5		ns
t_{EABWEH}	0.0		0.0		0.0		ns
$t_{EABWDSU}$	1.4		1.6		2.2		ns
t_{EABWDH}	0.0		0.0		0.0		ns
$t_{EABWASU}$	2.5		3.0		4.1		ns
t_{EABWAH}	0.0		0.0		0.0		ns
t_{EABWO}		6.2		7.5		9.9	ns

Notes to tables:
(1) All timing parameters are described in Tables 32 through 38 in this data sheet.
(2) Using an LE to register the signal may provide a lower setup time.
(3) This parameter is specified by characterization.

Tables 99 through 105 show EPF10K100A device internal and external timing parameters.

Table 99. EPF10K100A Device LE Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{LUT}		1.0		1.2		1.4	ns
t_{CLUT}		0.8		0.9		1.1	ns
t_{RLUT}		1.4		1.6		1.9	ns
t_{PACKED}		0.4		0.5		0.5	ns
t_{EN}		0.6		0.7		0.8	ns
t_{CICO}		0.2		0.2		0.3	ns
t_{CGEN}		0.4		0.4		0.6	ns
t_{CGENR}		0.6		0.7		0.8	ns
t_{CASC}		0.7		0.9		1.0	ns
t_{C}		0.9		1.0		1.2	ns
t_{CO}		0.2		0.3		0.3	ns
t_{COMB}		0.6		0.7		0.8	ns
t_{SU}	0.8		1.0		1.2		ns
t_{H}	0.3		0.5		0.5		ns
t_{PRE}		0.3		0.3		0.4	ns
t_{CLR}		0.3		0.3		0.4	ns
t_{CH}	2.5		3.5		4.0		ns
t_{CL}	2.5		3.5		4.0		ns

Notes to tables:
(1) All timing parameters are described in Tables 32 through 38 in this data sheet.
(2) Using an LE to register the signal may provide a lower setup time.
(3) This parameter is specified by characterization.

Tables 106 through 112 show EPF10K250A device internal and external timing parameters.

Table 106. EPF10K250A Device LE Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{LUT}		0.9		1.0		1.4	ns
t_{CLUT}		1.2		1.3		1.6	ns
t_{RLUT}		2.0		2.3		2.7	ns
t_{PACKED}		0.4		0.4		0.5	ns
t_{EN}		1.4		1.6		1.9	ns
t_{CICO}		0.2		0.3		0.3	ns
t_{CGEN}		0.4		0.6		0.6	ns
t_{CGENR}		0.8		1.0		1.1	ns
t_{CASC}		0.7		0.8		1.0	ns
t_{C}		1.2		1.3		1.6	ns
t_{CO}		0.6		0.7		0.9	ns
t_{COMB}		0.5		0.6		0.7	ns
t_{SU}	1.2		1.4		1.7		ns
t_{H}	1.2		1.3		1.6		ns
t_{PRE}		0.7		0.8		0.9	ns
t_{CLR}		0.7		0.8		0.9	ns
t_{CH}	2.5		3.0		3.5		ns
t_{CL}	2.5		3.0		3.5		ns

Notes to tables:
(1) All timing parameters are described in Tables 32 through 37 in this data sheet.
(2) Using an LE to register the signal may provide a lower setup time.
(3) This parameter is specified by characterization.

ClockLock & ClockBoost Timing Parameters

For the ClockLock and ClockBoost circuitry to function properly, the incoming clock must meet certain requirements. If these specifications are not met, the circuitry may not lock onto the incoming clock, which generates an erroneous clock within the device. The clock generated by the ClockLock and ClockBoost circuitry must also meet certain specifications. If the incoming clock meets these requirements during configuration, the ClockLock and ClockBoost circuitry will lock onto the clock during configuration. The circuit will be ready for use immediately after configuration. Figure 31 illustrates the incoming and generated clock specifications.

Figure 31. Specifications for the Incoming & Generated Clocks

The t_I parameter refers to the nominal input clock period; the t_O parameter refers to the nominal output clock period.

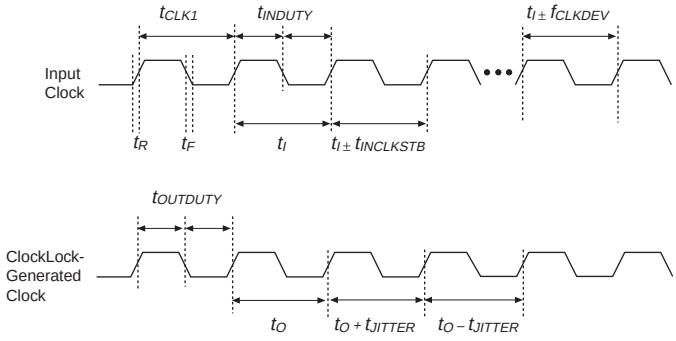


Table 113 summarizes the ClockLock and ClockBoost parameters.

Table 113. ClockLock & ClockBoost Parameters (Part 1 of 2)

Symbol	Parameter	Min	Typ	Max	Unit
t_R	Input rise time			2	ns
t_F	Input fall time			2	ns
t_{INDUTY}	Input duty cycle	45		55	%
f_{CLK1}	Input clock frequency (ClockBoost clock multiplication factor equals 1)	30		80	MHz
t_{CLK1}	Input clock period (ClockBoost clock multiplication factor equals 1)	12.5		33.3	ns
f_{CLK2}	Input clock frequency (ClockBoost clock multiplication factor equals 2)	16		50	MHz
t_{CLK2}	Input clock period (ClockBoost clock multiplication factor equals 2)	20		62.5	ns